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(cont.)
11. (New) The structure according to claim 9, wherein said shape comprises one of a square and a rectangle, said shape having a side with a length in a range from 200 to 800 μm .

12. (New) The structure according to claim 9, wherein said separating layer has a thickness of about 5.5 μm .

13. (New) The structure according to claim 9, wherein a distance between adjacent ones of said openings is about 50 μm .

14. (New) The structure according to claim 9, further comprising:
a metal nitride undercoat layer formed over said substrate in said plurality of openings.

15. (New) The structure according to claim 9, wherein each opening of said plurality of openings has a rounded shape.

16. (New) The structure according to claim 9, wherein said separating layer is formed directly on said substrate.

17. (New) A method of forming a semiconductor device structure having a first portion and a plurality of second portions, said method comprising:

forming a separating layer over a substrate;

forming a mask over said separating layer;

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etching said separating layer using said mask to create a plurality of openings in said separating layer; and

rounding at least one opening in said plurality of openings such that said at least one opening has a rounded shape.

18. (New) The method according to claim 17, wherein said forming said separating layer over said substrate comprises forming said separating layer directly on said substrate, and

wherein said forming said mask over said separating layer comprises forming said mask directly on said separating layer. - -